		Operato r	Plural s	Time Stamp
(SOI (silicon near5 insulat\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 19:27
1 and (source drain)	US-PGPU B; USPAT; USOCR	OR	ON ·	2005/06/21 19:27
2 and gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 19:28
(STI (shallow near5 trench near5 isolat\$3))	US-PGPU B; USPAT; USOCR	OR	ON É	2005/06/21 19:28
3 and 4	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 16:33
5 and epitaxial\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 16:33
6 and trench	US-PGPU B; USPAT; USOCR	OR .	ON	2005/06/21 16:33
6 and (trench recess groove)	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 16:34
8 and (thermal near8 oxid\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 16:34
8 and (thermal\$3 near8 oxid\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 16:34
9 and 10	US-PGPU B; USPAT; USOCR	OR	ON	2005/06/21 16:35
(SOI (silicon near5 insulat\$3))	EPO; JPO; DERWENT ;	OR	ON	2005/06/21 19:27
12 and (source drain)	IBM_TDB EPO; JPO; DERWENT ;	OR	ON	2005/06/21 19:28
13 and gate	IBM_TDB EPO; JPO; DERWENT	OR	ON	2005/06/21 19:28
12	2 and (source drain)	; IBM_TDB  Pand (source drain)  EPO; JPO; DERWENT; IBM_TDB  Band gate  EPO; JPO;	; IBM_TDB EPO; JPO; DERWENT ; IBM_TDB EPO; JPO; DERWENT ; IBM_TDB EPO; JPO; DERWENT ;	; ; iBM_TDB EPO; JPO; DERWENT; iBM_TDB EPO; JPO; DR ON ON DERWENT; OR DERWENT;

L15	61	14 and (STI (shallow near5 trench near5 isolat\$3))	EPO; JPO; DERWENT	OR	ON	2005/06/21 19:29
			; IBM_TDB		:	